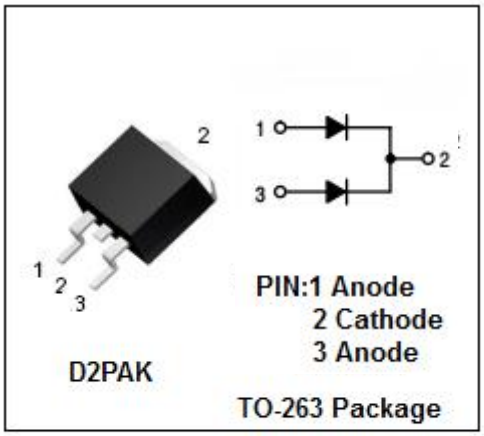
Schottky Barrier Rectifier — MBRB3035CT



FEATURES

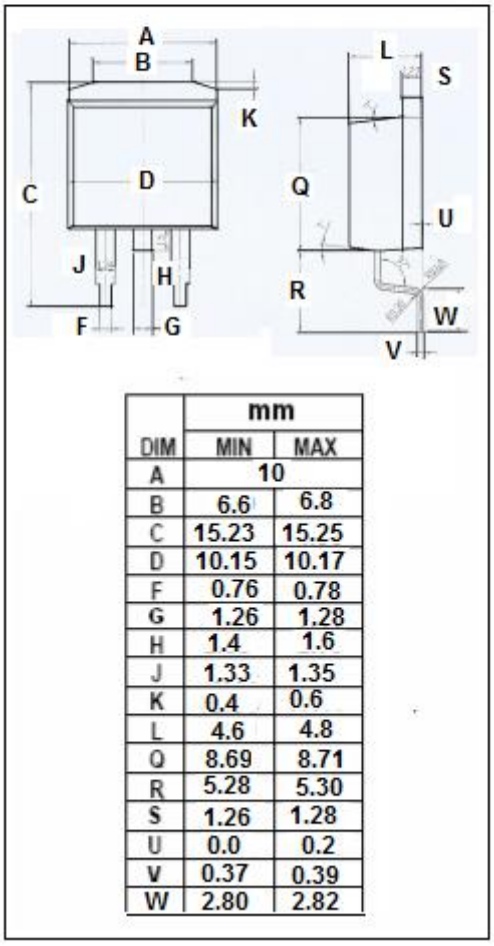
- Schottky Barrier Chip
- Dual Rectifier Conduction
- Low Power Loss/High Efficiency
- High Current Capability, Low Forward Voltage Drop
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low-voltage,high frequency inverters，free wheeling and polarrity protection applications .

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	35	V
$V_{R(RMS)}$	RMS Reverse Voltage	24.5	V
$I_{F(AV)}$	Average Rectified Forward Current (Rated V_R) T_C= 100℃	30	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	200	A
T_J	Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~175	℃
dv/dt	Voltage Rate of Change (Rated V_R)	10,000	V/μs



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

Schottky Barrier Rectifier MBRB3035CT

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.5	℃/W

ELECTRICAL CHARACTERISTICS(Pulse Test: Pulse Width≤300μs,Duty Cycle≤2%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 15A ; T_C= 25℃ I_F= 30A ; T_C= 25℃ I_F= 30A ; T_C= 125℃	0.70 0.84 0.72	V
I_R	Maximum Instantaneous Reverse Current	Rated DC Voltage, T_C= 25℃ Rated DC Voltage, T_C= 125℃	0.2 40	mA